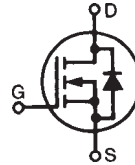


Polar™ HiperFET™ Power MOSFET

IXFP4N100PM

$$\begin{aligned} V_{DSS} &= 1000V \\ I_{D25} &= 2.5A \\ R_{DS(on)} &\leq 3.3\Omega \end{aligned}$$

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

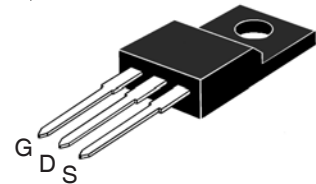


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	1000	V
V_{DGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}, R_{GS} = 1\text{ M}\Omega$	1000	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	2.5	A
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM}	8.0	A
I_A	$T_C = 25^\circ\text{C}$	4.0	A
E_{AS}	$T_C = 25^\circ\text{C}$	200	mJ
dv/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J = 150^\circ\text{C}$	10	V/ns
P_D	$T_C = 25^\circ\text{C}$	57	W
T_J		- 55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		- 55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from Case for 10 s	300	$^\circ\text{C}$
T_{SOLD}	Plastic Body for 10 s	260	$^\circ\text{C}$
M_d	Mounting Torque	1.13/10	Nm/lb.in.
Weight		2.5	g

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Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu\text{A}$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	3.0		6.0 V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			$\pm 100\text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			10 μA 750 μA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 2A$, Note 1			3.3 Ω

OVERMOLDED



G = Gate D = Drain
S = Source

Features

- Plastic Overmolded Tab for Electrical Isolation
- Avalanche Rated
- Fast Intrinsic Diode
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Laser Drivers
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{V}, I_D = 2\text{A}$, Note 1	1.8	3.0	S
C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		1456	pF
C_{oss}			90	pF
C_{rss}			16	pF
R_{Gi}	Gate Input Resistance		1.6	Ω
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 2\text{A}$ $R_G = 5\Omega$ (External)		24	ns
t_r			36	ns
$t_{d(off)}$			37	ns
t_f			50	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 2\text{A}$		26	nC
Q_{gs}			9	nC
Q_{gd}			12	nC
R_{thJC}				2.2°C/W

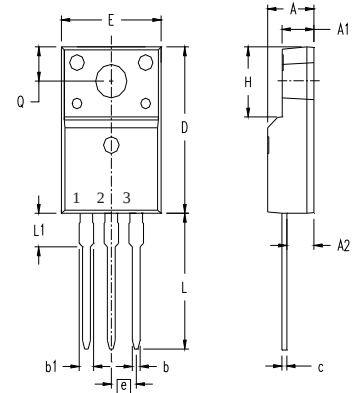
Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			4 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			16 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{V}$, Note 1			1.3 V
t_{rr}	$I_F = 2\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$			300 ns
Q_{RM}			0.34	μC
I_{RM}			5.30	A

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Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

ISOLATED TO-220 (IXFP...M)



Terminals: 1 - Gate
2 - Drain
3 - Source

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.177	.193	4.50	4.90
A1	.092	.108	2.34	2.74
A2	.101	.117	2.56	2.96
b	.028	.035	0.70	0.90
b1	.050	.058	1.27	1.47
c	.018	.024	0.45	0.60
D	.617	.633	15.67	16.07
E	.392	.408	9.96	10.36
e	.100 BSC		2.54 BSC	
H	.255	.271	6.48	6.88
L	.499	.523	12.68	13.28
L1	.119	.135	3.03	3.43
$\varnothing P$	.121	.129	3.08	3.28
Q	.126	.134	3.20	3.40

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

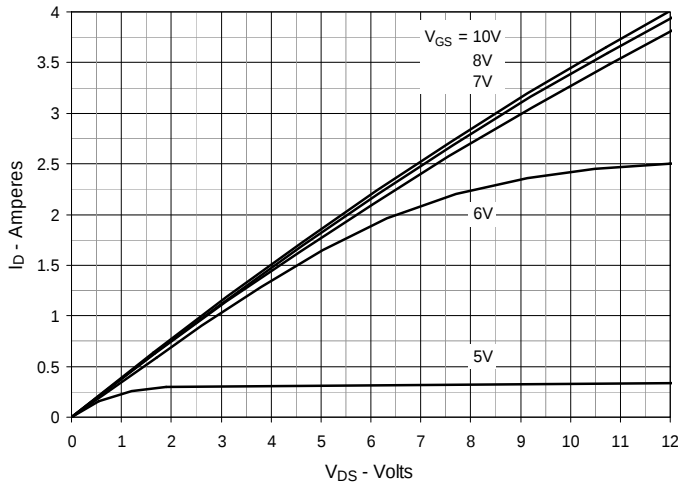


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

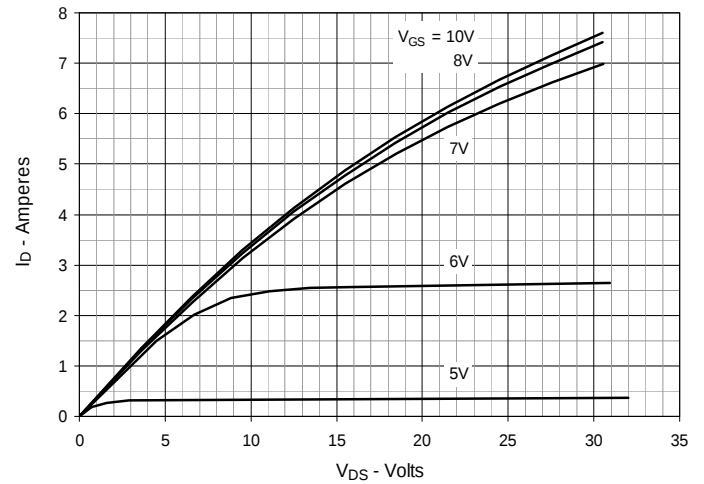


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

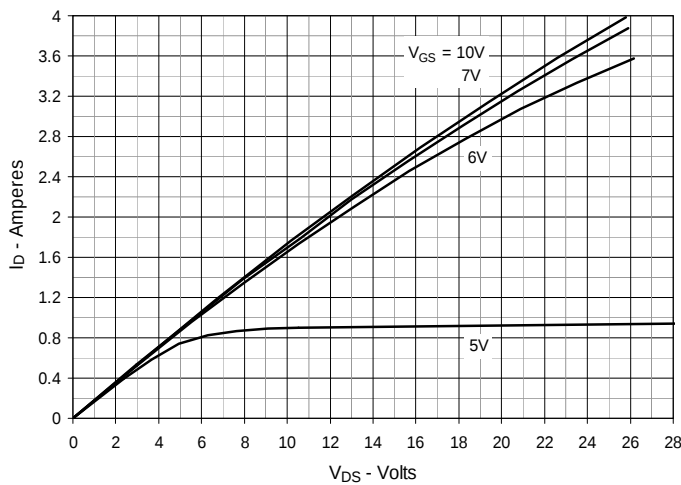


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 2\text{A}$ Value vs. Junction Temperature

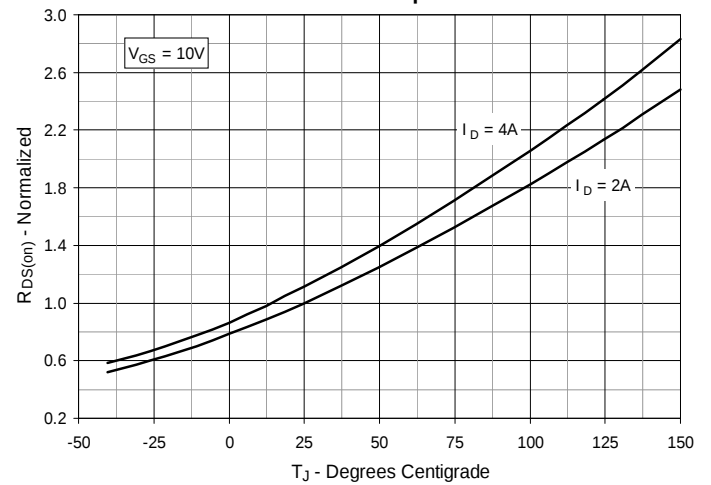


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 2\text{A}$ Value vs. Drain Current

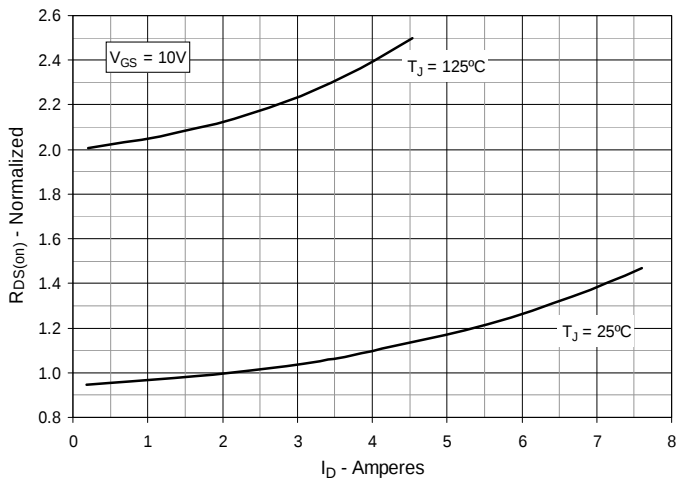


Fig. 6. Maximum Drain Current vs. Case Temperature

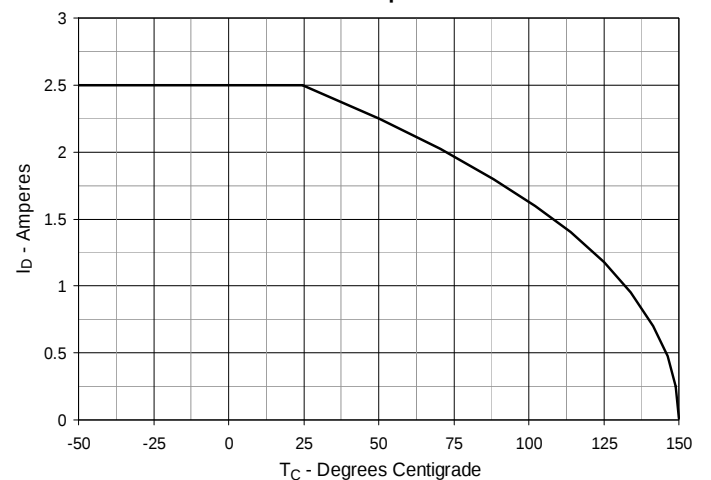


Fig. 7. Input Admittance

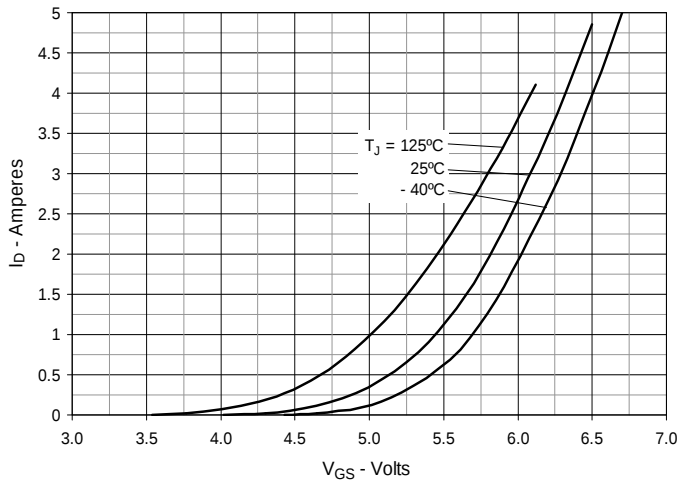


Fig. 8. Transconductance

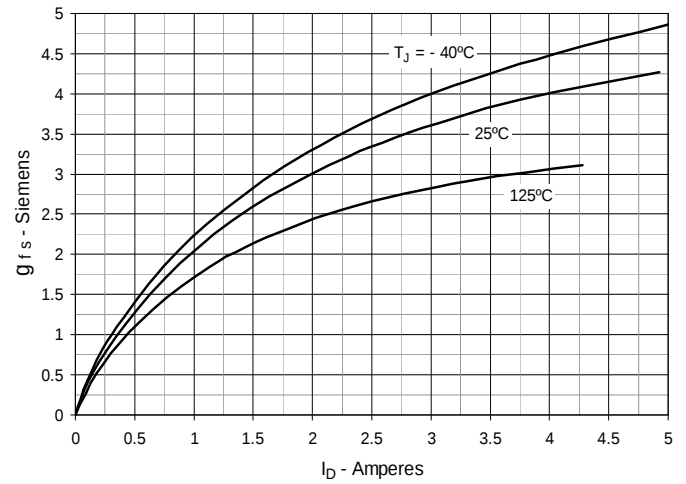


Fig. 9. Forward Voltage Drop of Intrinsic Diode

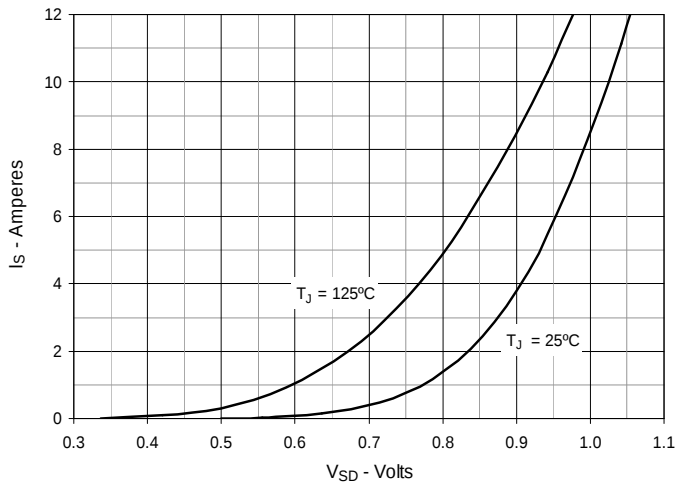


Fig. 10. Gate Charge

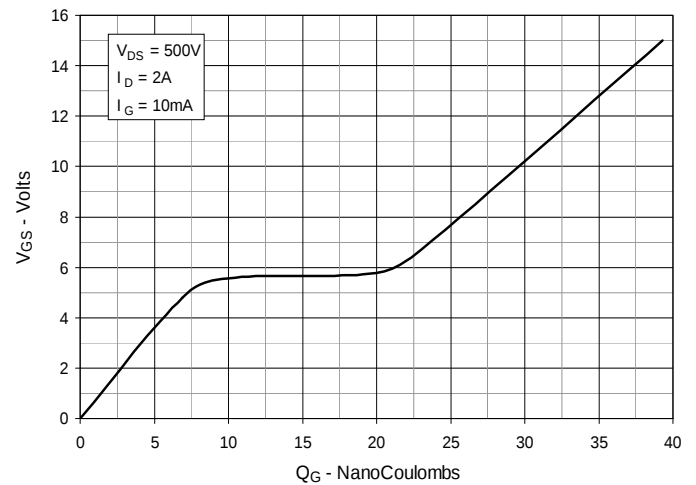


Fig. 11. Capacitance

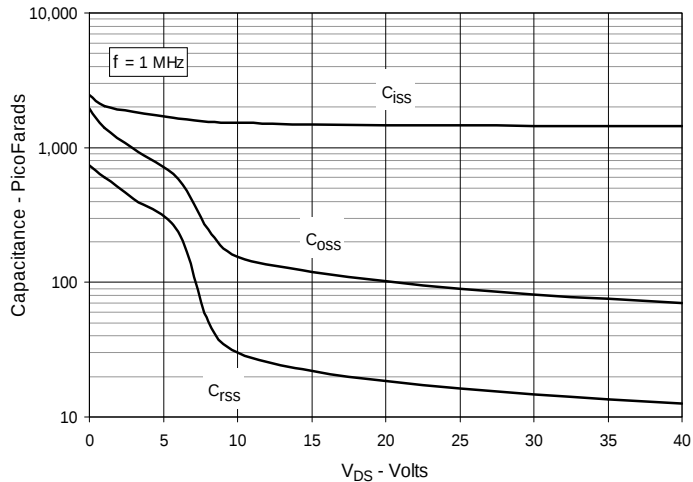


Fig. 12. Maximum Transient Thermal Impedance

